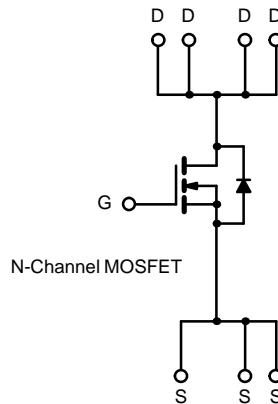
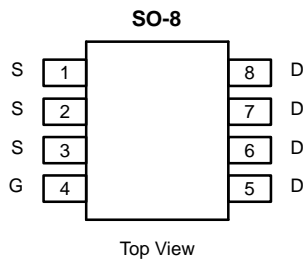




N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0075 @ $V_{GS} = 10$ V	± 15
	0.010 @ $V_{GS} = 4.5$ V	± 13

TrenchFET[®]
Power MOSFETs
High-Efficiency
PWM Optimized



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^{a, b}	I_D	$T_A = 25^\circ\text{C}$	± 15
		$T_A = 70^\circ\text{C}$	± 13
Pulsed Drain Current	I_{DM}	± 50	A
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	2.3	
Maximum Power Dissipation ^{a, b}	P_D	$T_A = 25^\circ\text{C}$	3.10
		$T_A = 70^\circ\text{C}$	2
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	33	40
		Steady State	68	80
Maximum Junction-to-Foot	R_{thJC}	16	21	$^\circ\text{C/W}$

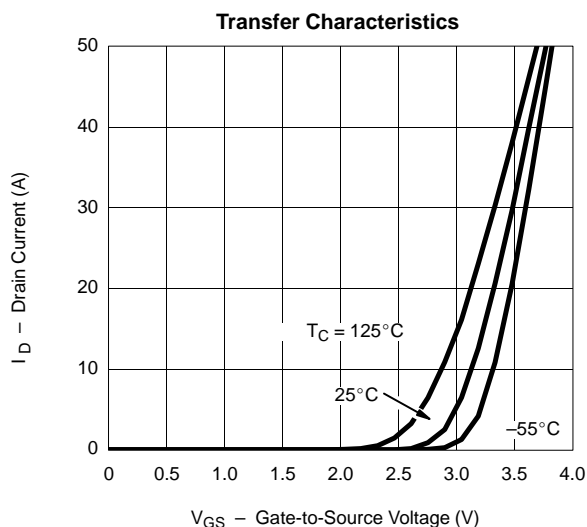
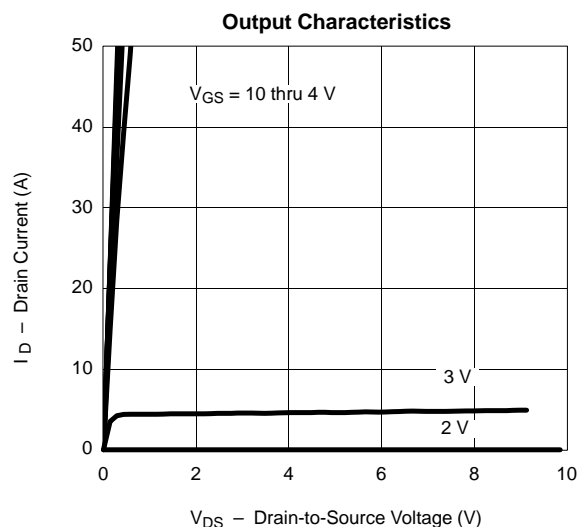
Notes
a. Surface Mounted on FR4 Board.
b. $t \leq 10$ sec.


MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		0.0062	0.0075	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}$		0.0083	0.010	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}$		40		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.73	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 5.0 \text{ V}, I_D = 15 \text{ A}$		35	45	nC
Gate-Source Charge	Q_{gs}			12.2		
Gate-Drain Charge	Q_{gd}			11.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 6 \Omega$		20	30	ns
Rise Time	t_r			16	25	
Turn-Off Delay Time	$t_{d(off)}$			120	180	
Fall Time	t_f			43	65	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		50	80	

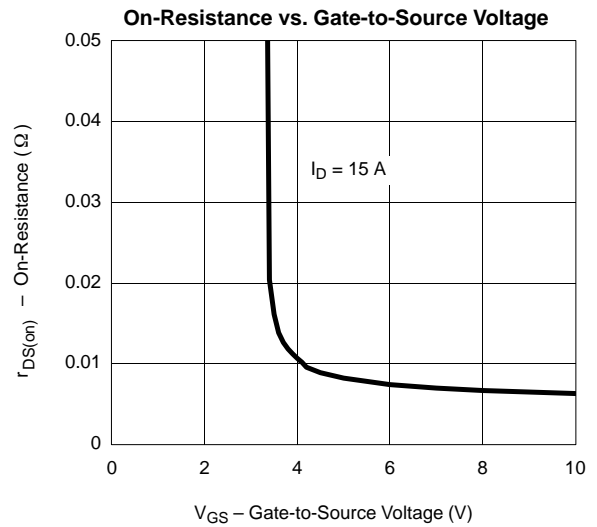
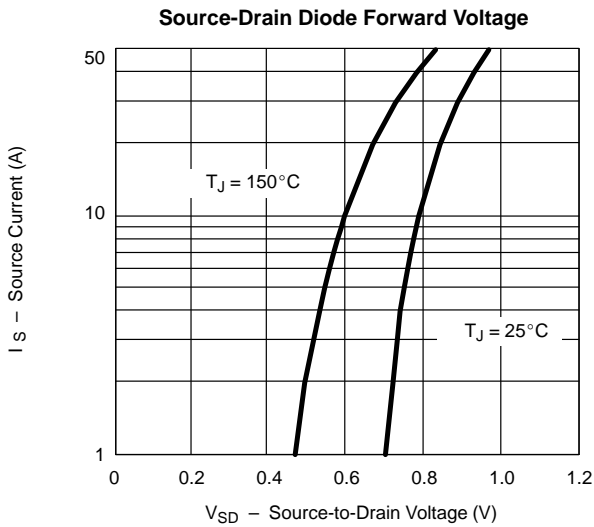
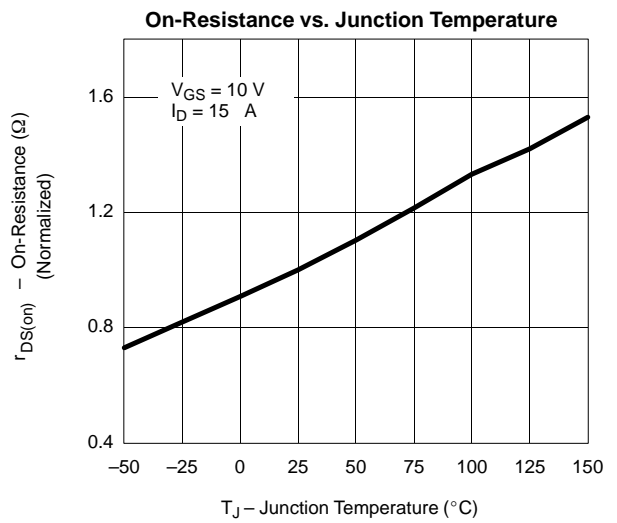
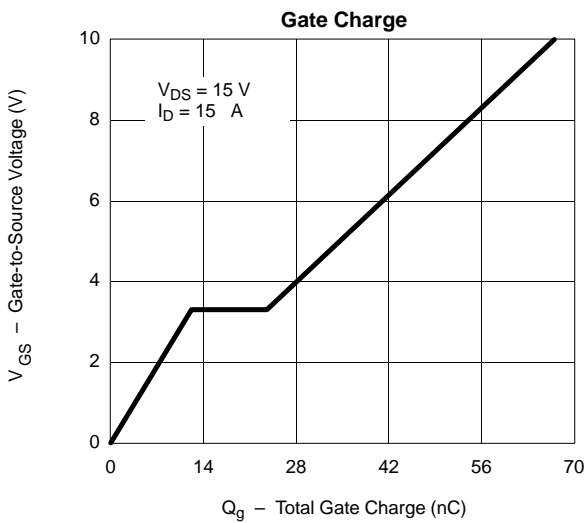
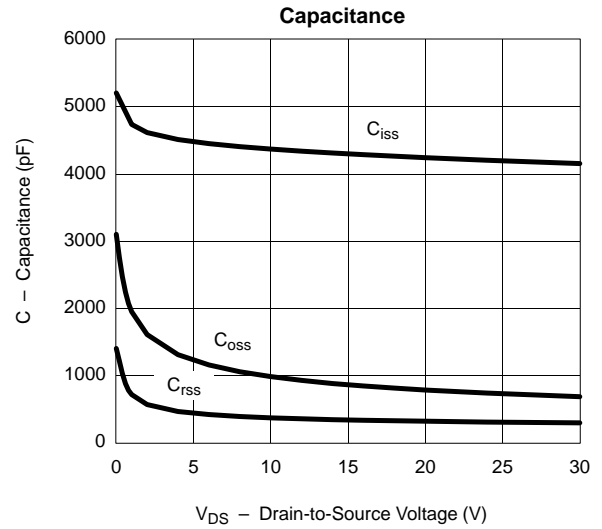
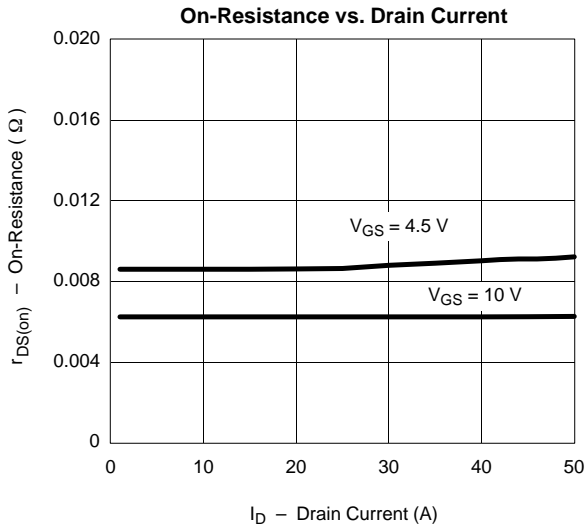
Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)




TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

